

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING SAME, AND MEMORY

ABSTRACT

Disclosed in the embodiments of the present disclosure are a semiconductor structure and method for manufacturing same, and a memory. The semiconductor structure includes: a plurality of first active columns arranged in an array along a first direction and a second direction, a plurality of first electrodes located in first grooves arranged at intervals, a plurality of first dielectric layers, and a second electrode covering surfaces of the first dielectric layers. The first direction and the second direction are perpendicular to the extension direction of the first active column, and the first direction is intersected with the second direction. Each first electrode covers a side wall of one of the first active columns. Each first groove surrounds a surface of each first active column. Each first dielectric layer covers the side wall of one of the first electrodes and a bottom of a gap between two adjacent first electrodes.

[Fig. 2]